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(71) Applicant: SEMICONDUCTOR ENERGY LAB

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SEMICONDUCTOR DEVICE (54) PRODUCTION OF

(57) Abstract:

disilane or trisilane and crystalizing it single crystal semiconductor layer on a silicon oxide film that is formed by performance by forming a true nona low-pressure CVD method using at a specific low temperature. PURPOSE: To obtain a high

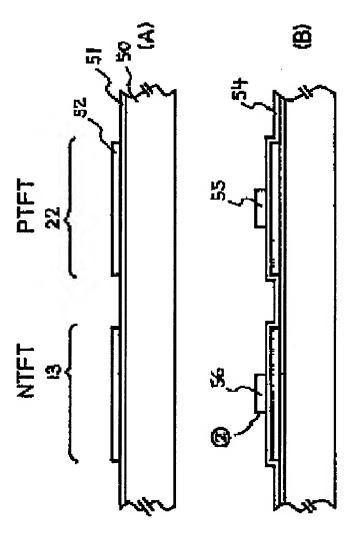
on a glass 50 that is inexpensive such film is formed as a blocking layer 51 CONSTITUTION: A silicon oxide

of 450-700°C, and a silicon film 52 is a slicon film in an amorphous state is atmosphere of non-oxide for 12 to 70 changed from an amorphous structure pressure vapor method at 450-550°C crystalization temerature. Then, after nours at an intermediate temperature without grain boundary. The film 52 area 22 for a PTHT is formed on the right side of the glass 50 and an area respectively, then gate electrodes 55 formed, it is entirely annealed in an s subjected to photoetching, and an through for film formation by a low and 56 are formed thereon by using withstand the heat treatment of at that is 100-200°C lower than the obtaining higher carrier mobility frequency sputtering method. A disilane or trisilane is supplied the silicon oxide film as a gate to higher-order state, thereby as quartz glass, etc., and can most 700°C, by using a high 13 on the left side thereof, insulation film 54.

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